# RACAH PARAMETER

M. Sc.: CC – 3 (Inorganic Chemistry)

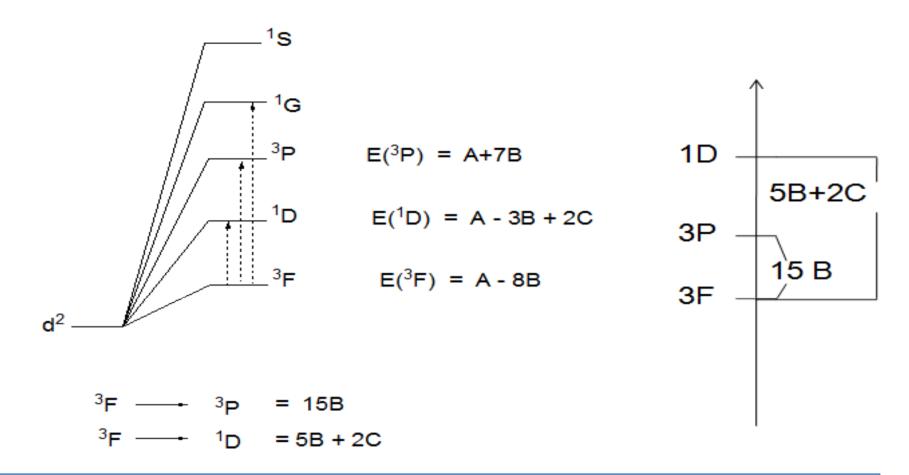
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#### **Racah Parameter**

- Racah Parameter is the energy gap between two spectroscopic terms due to e-e repulsion.
- ➤ It is denoted by B & C.
- Energy gap between two spectroscopic terms of same multiplicity like <sup>3</sup>F, <sup>3</sup>P or <sup>4</sup>F, <sup>4</sup>P etc is expressed by B.
- Energy gap between two spectroscopic term of different multiplicity like <sup>3</sup>P, <sup>1</sup>D or <sup>4</sup>F, <sup>2</sup>D, <sup>3</sup>G etc is expressed by B & C.
- > Racah parameters after Giulio Racah, who first described them.
- ➤It describes the repulsion energy associated with an electronic term.
- $\triangleright$  the interelectronic repulsion of a <sup>3</sup>P term is A + 7B,
- ><sup>3</sup>F term is A 8B,
- > 1D = A 3B + 2C
- ► Difference between  ${}^{3}F \& {}^{3}P = (A+7B) (A-8B) = 15B$ .
- Similarly difference between  ${}^{3}F \& {}^{1}D = (A-8B) (A-3B+2C) = 5B+2C$

#### Racah Inter-electronic Repulsion Parameters (B, C)



When ligand approaches to the free metal ion than e-e repulsion is decreased & hence energy gap becomes low & resulting gap also decreased in complex compound i.e. B free ion is greater than B complex.

#### **Reason of Racah Parameter**

When an <u>atom</u> has more than one <u>electron</u> there will be some <u>electrostatic</u> repulsion between those electrons. The amount of repulsion varies from atom to atom, depending upon the number and <u>spin</u> of the electrons and its energy level of the <u>orbitals</u> they occupy.

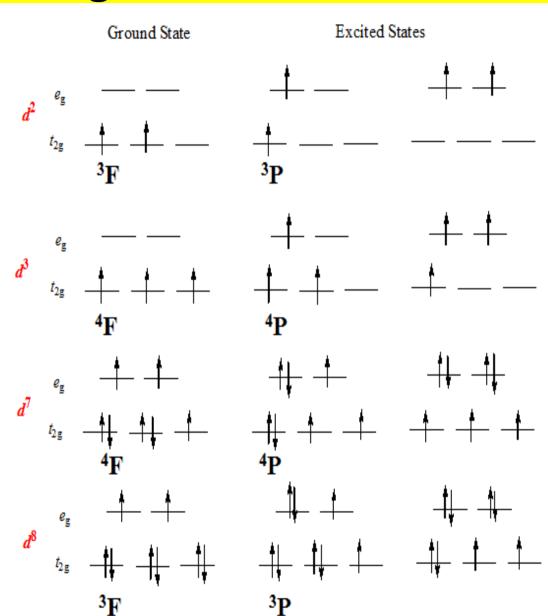
## **Electronic State & in ground & Excited State**

Triple degeneracy of a  $d^2$  ion's  ${}^3T_{2g}$  ground state due to three possible sites for hole in  $t_{2g}$  level

Singly degenerate  ${}^3\mathrm{T}_{2\mathrm{g}}$  ground state. Only one possible arrangement for three electrons in  $t_{2\mathrm{g}}$  level

Triple degenerate ground state for  $d^7$ Three possible sites for hole in  $t_{2g}$  level

Singly degenerate  ${}^{3}\text{T}_{2g}$  ground state. Only one possible arrangement for six  $t_{2g}$  electrons.



Configuration	Term symbols
$d^1, d^9$	$2_{ m D}$
$\mathbf{d}^2$ , $\mathbf{d}^8$	<sup>3</sup> F, <sup>3</sup> P, <sup>1</sup> G, <sup>1</sup> D, <sup>1</sup> S
$d^3$ , $d^7$	<sup>4</sup> F, <sup>4</sup> P, <sup>2</sup> H, <sup>2</sup> G, <sup>2</sup> F, <sup>2</sup> D <sub>2</sub> , <sup>2</sup> P
$\mathbf{d^4},\mathbf{d^6}$	<sup>5</sup> D, <sup>3</sup> H, <sup>3</sup> G, <sup>3</sup> F <sub>2</sub> , <sup>3</sup> D, <sup>3</sup> P <sub>2</sub> , <sup>1</sup> I, <sup>1</sup> G <sub>2</sub> , <sup>1</sup> D <sub>2</sub> , <sup>1</sup> S <sub>2</sub>
<sub>d</sub> 5	<sup>6</sup> S, <sup>4</sup> G, <sup>4</sup> D, <sup>4</sup> P, <sup>2</sup> I, <sup>2</sup> H, <sup>2</sup> G <sub>2</sub> , <sup>2</sup> F <sub>2</sub> , <sup>2</sup> D <sub>3</sub> , <sup>2</sup> P, <sup>2</sup> S

Repulsion also occurs between the terms of same spin multiplicity & gives different energy level. The total repulsion can be expressed in terms of three parameters A, B and C.

### **Nephelauxetic Effect/**

### Electron cloud expension/Nephelauxetic Parameter

- ➤It is electron repulsion found in complexes due to e-e repulsion.
- ►It is denoted by ß (Nephelauxetic parameter)
- ➤ It is expressed by
- $\triangleright \beta$  is always less than 1
- It means B complex is less than B free ion.
- It means energy gap between two terms in free ion is greater than that of its complex form.
- ➤ i.e. e-e repulsion between two electrons in free ion is greater than its complex.
- ➤ When ligand approaches to the free ion than e-e repulsion is decreased & hence nephelauxetic parameter is decreased.
- ➤ It determines covalent character in complex compound.

